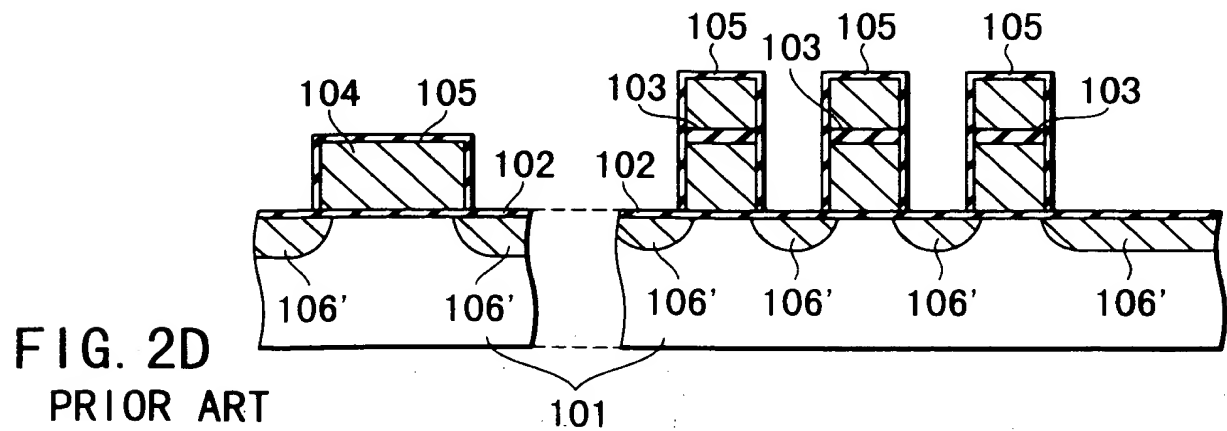
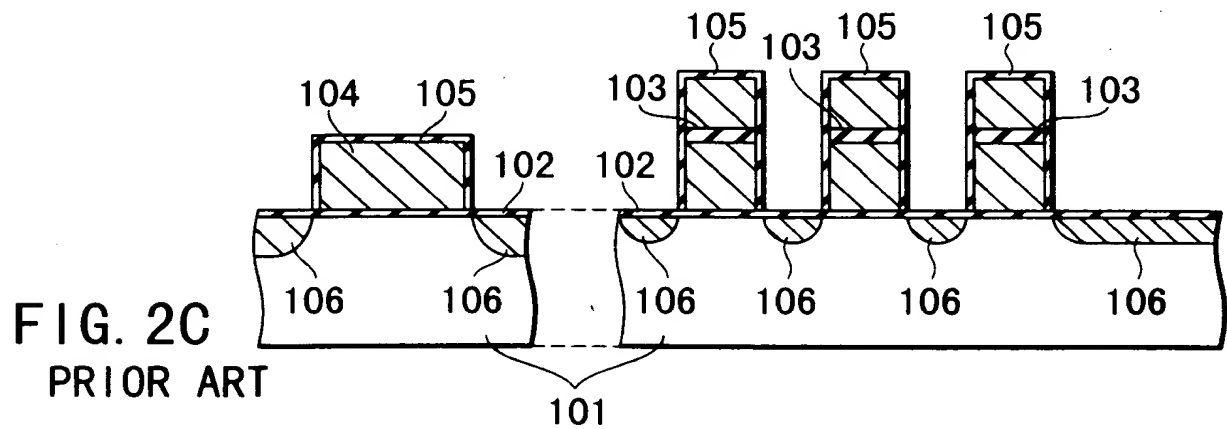
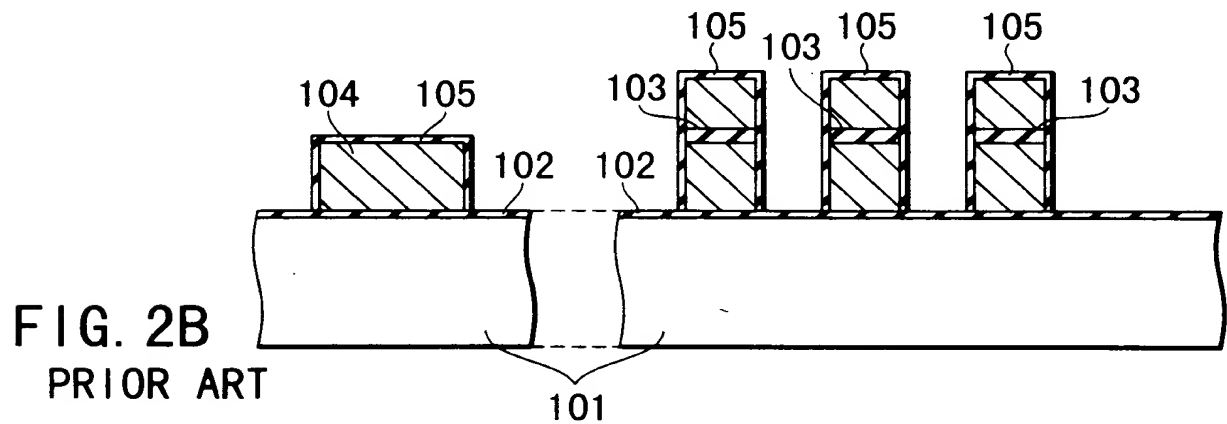
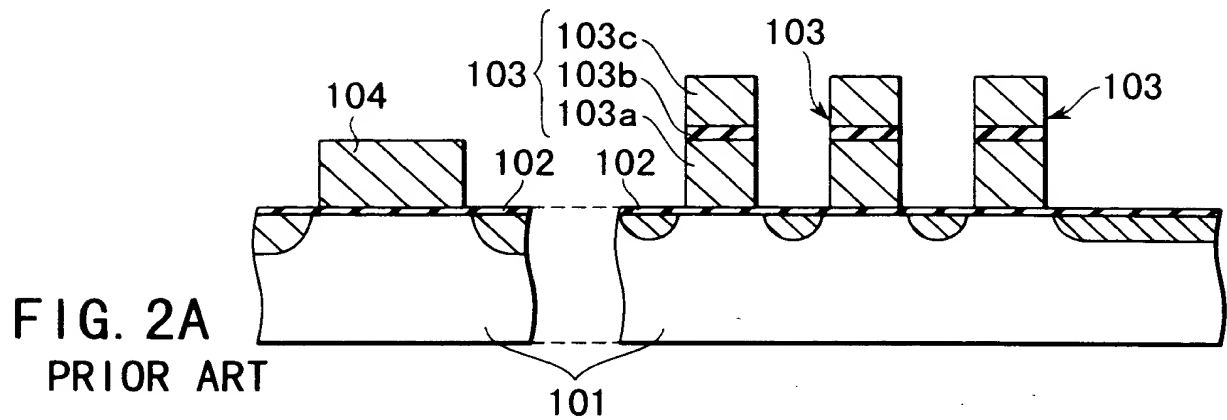


FIG. 1
PRIOR ART



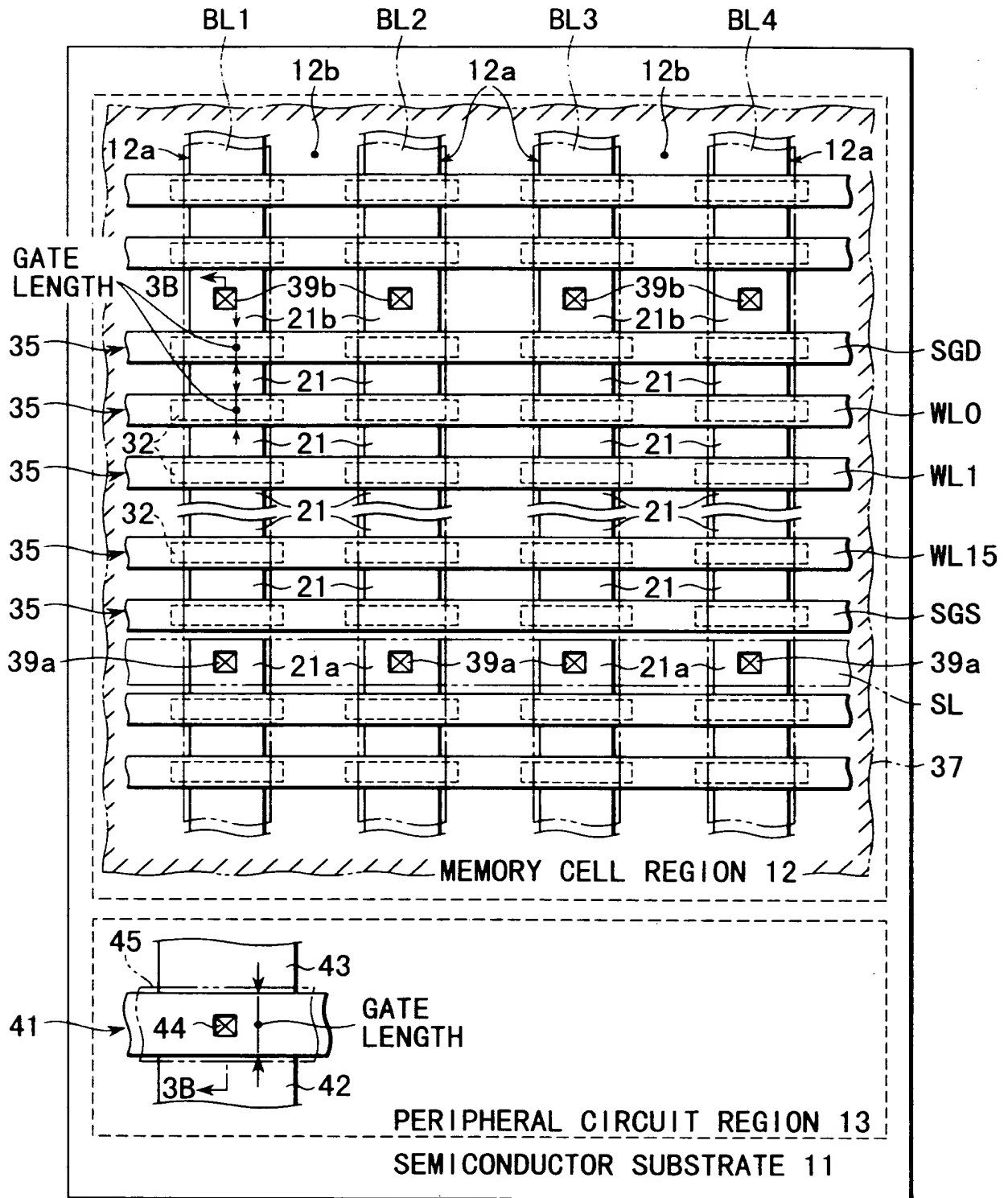


FIG. 3A

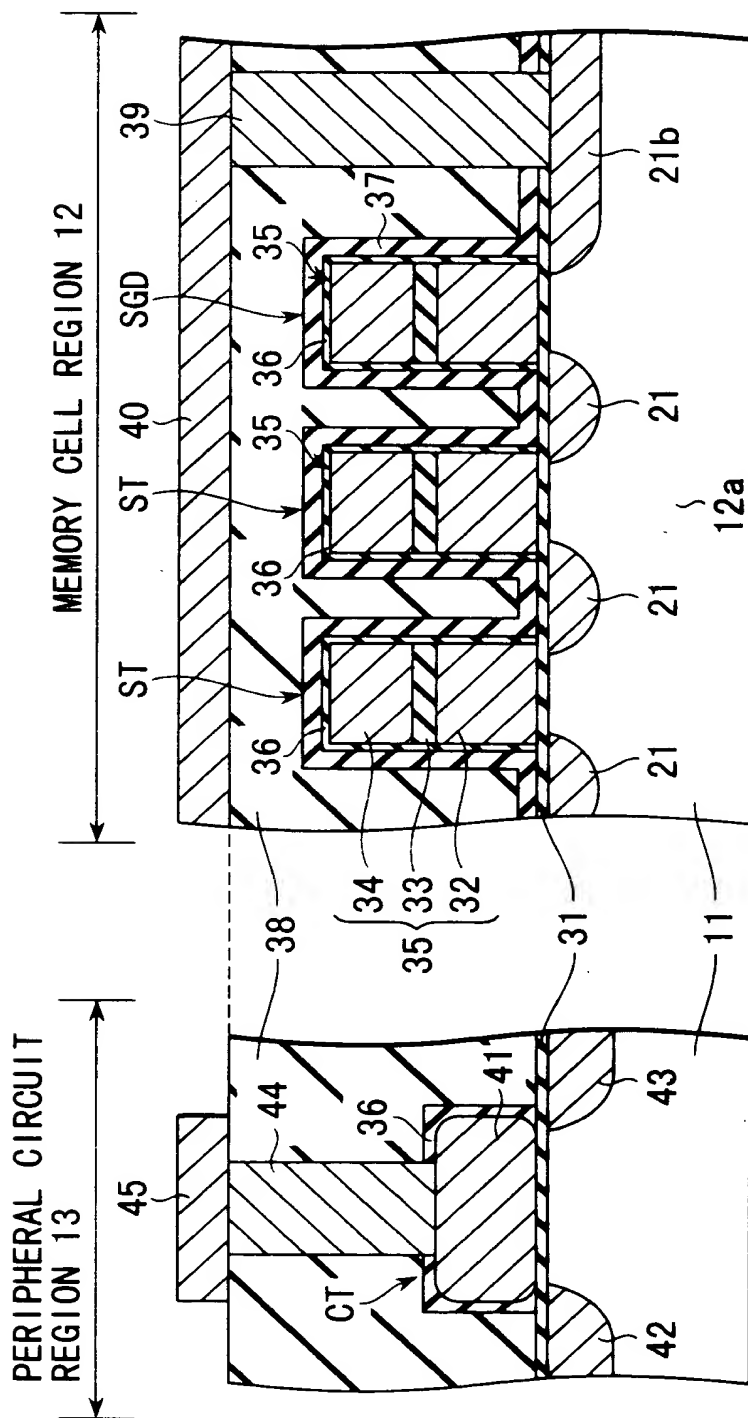
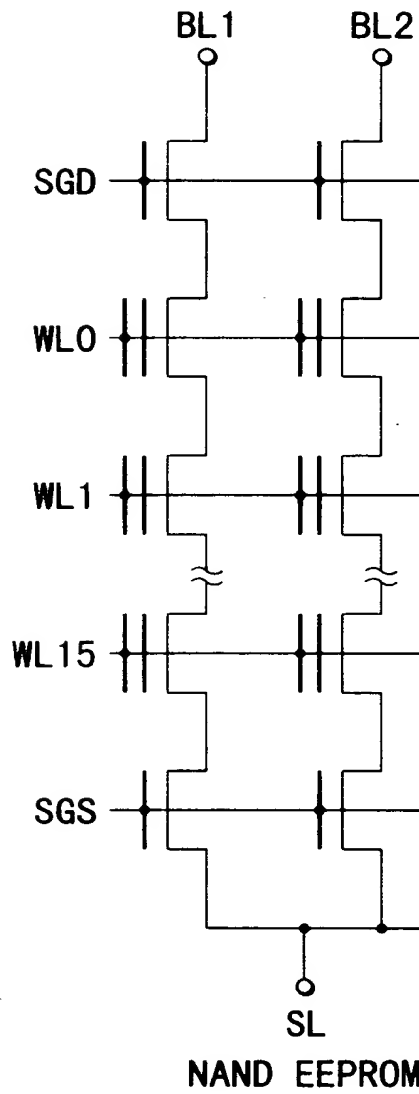


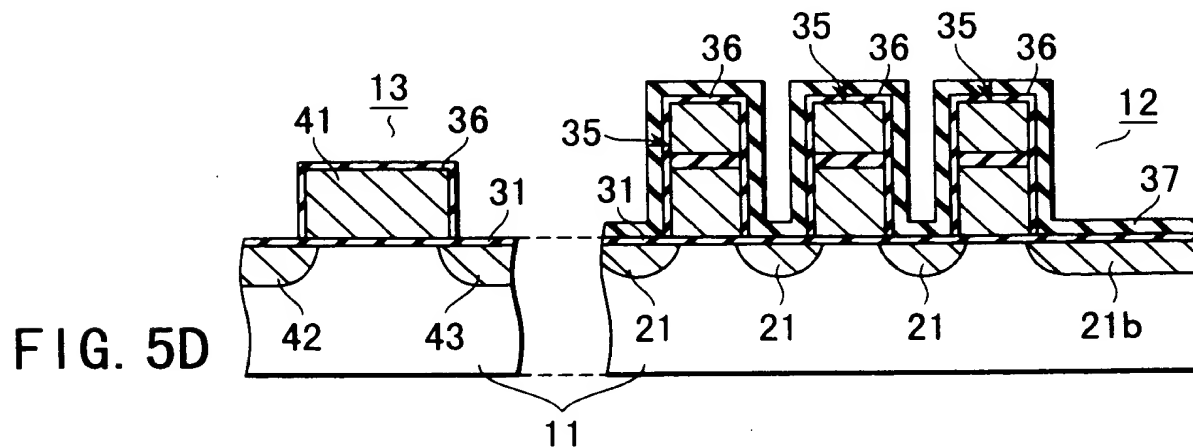
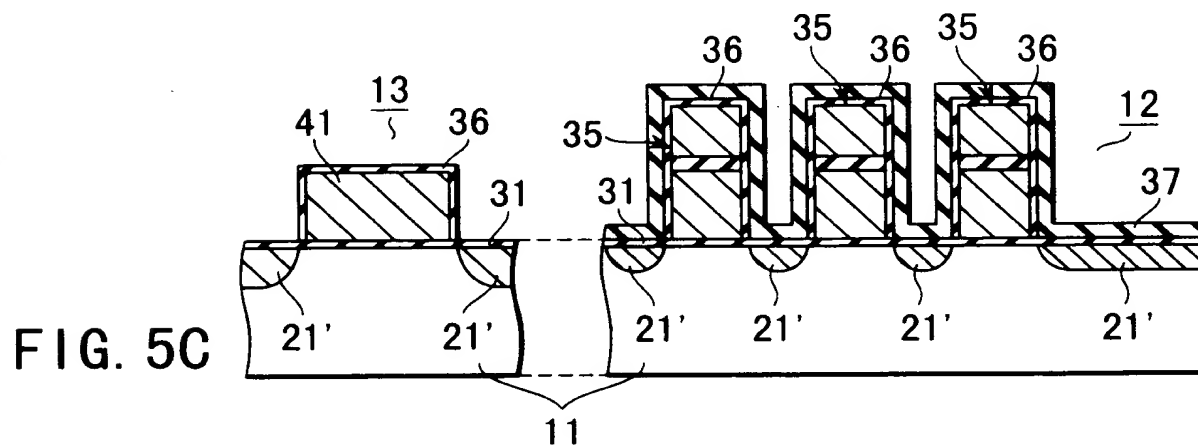
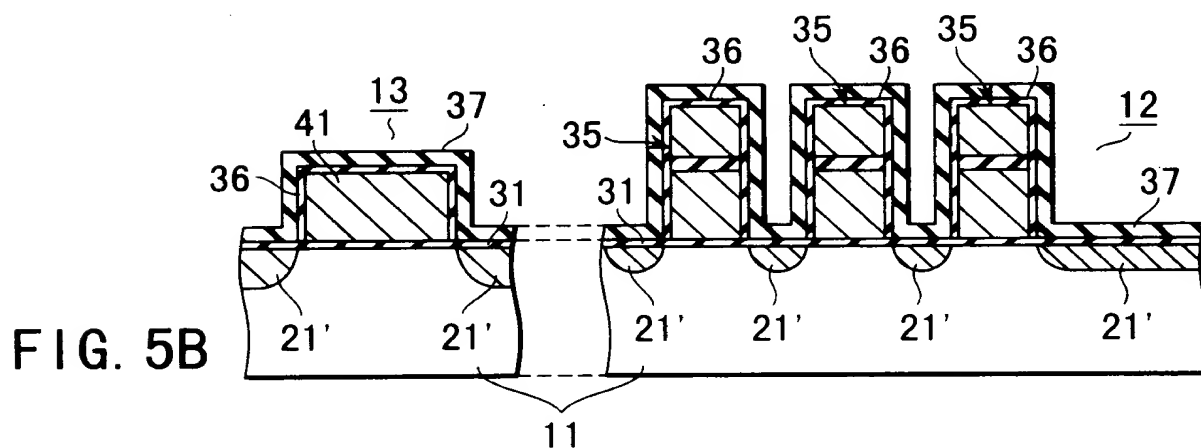
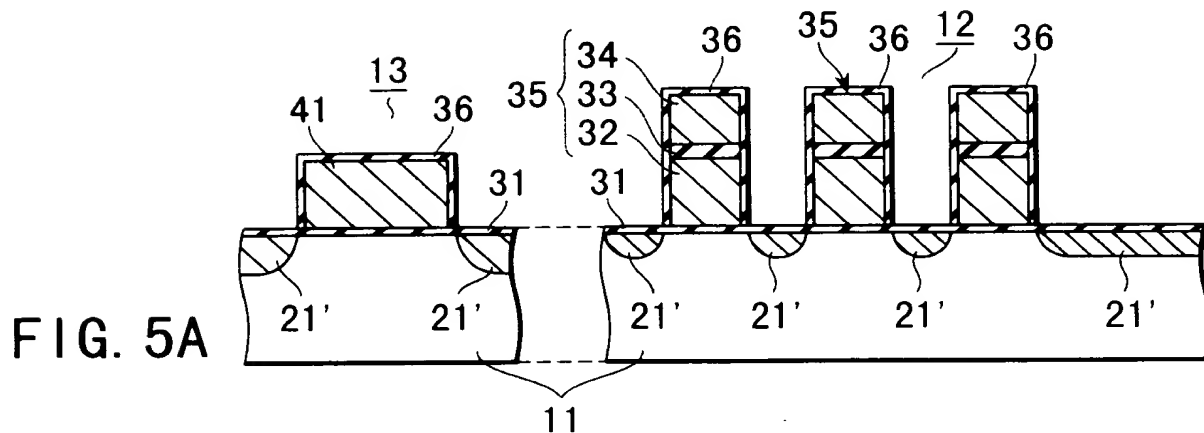
FIG. 3B



NAND EEPROM

FIG. 4

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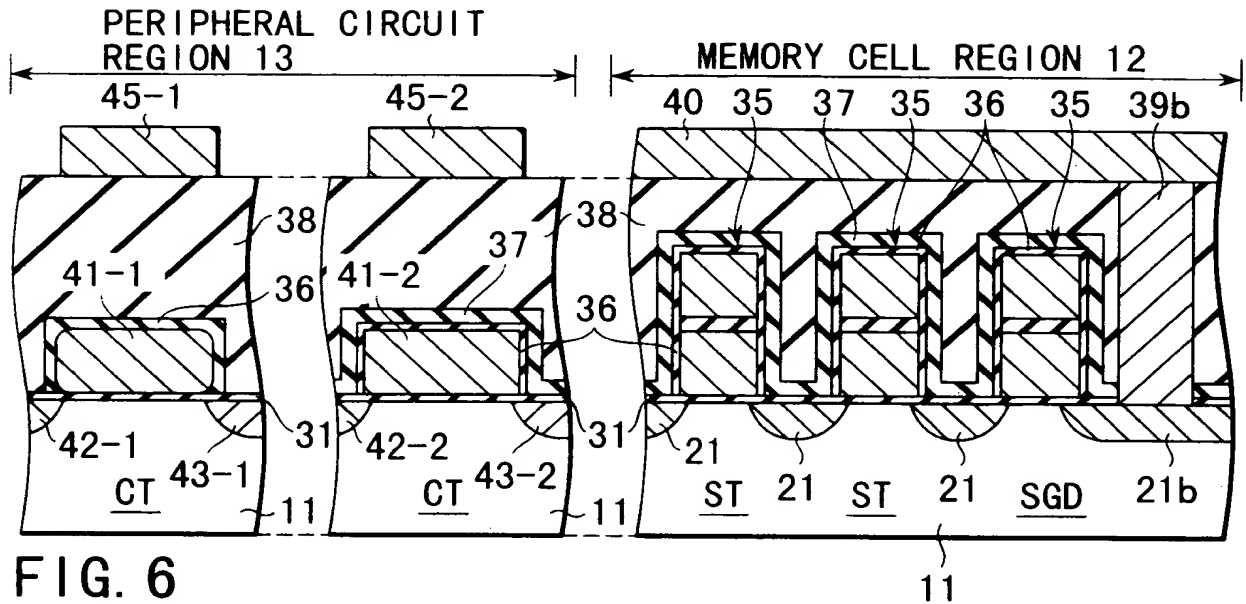


FIG. 6

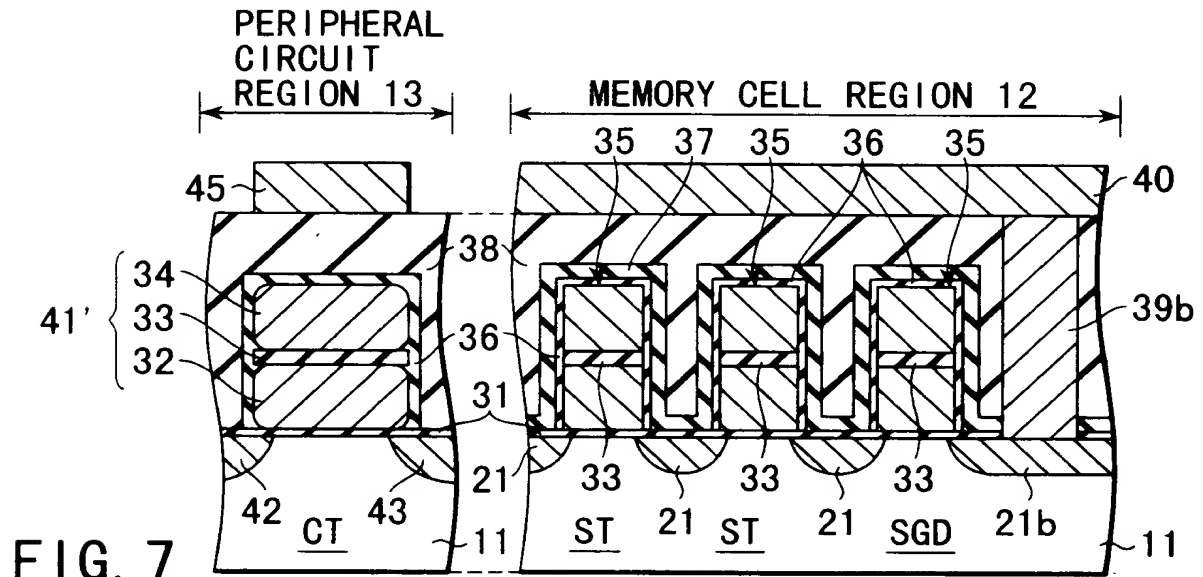


FIG. 7

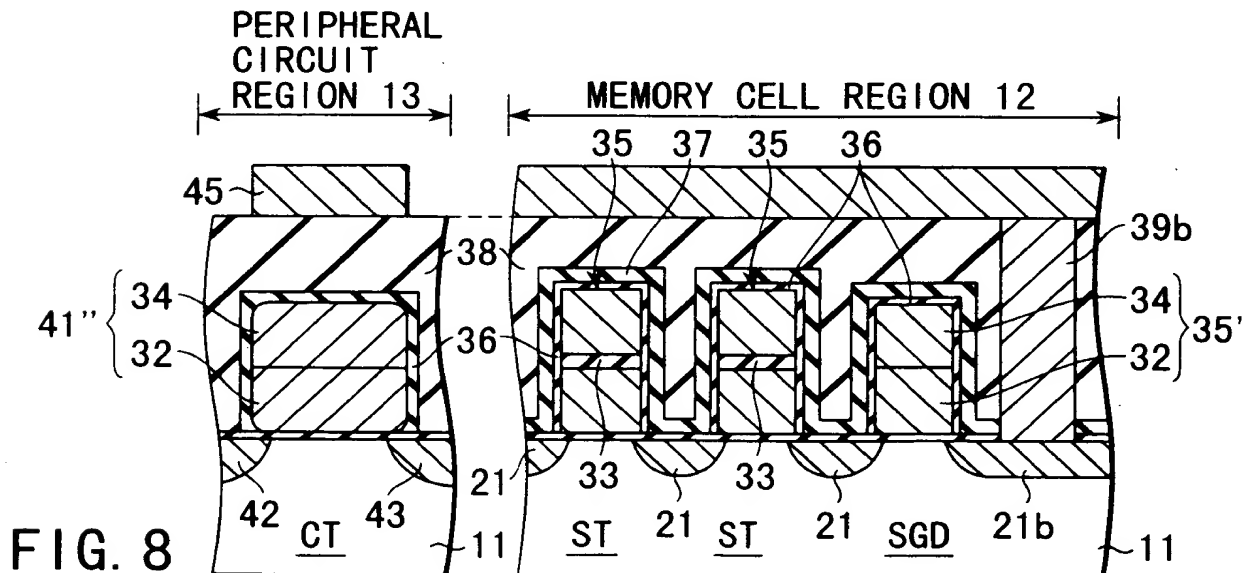


FIG. 8

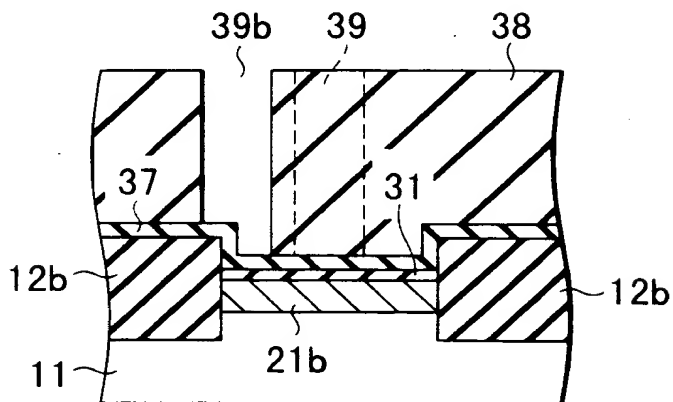


FIG. 9A

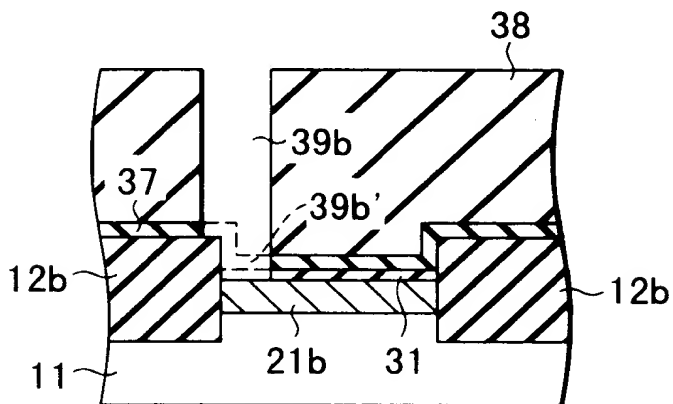


FIG. 9B

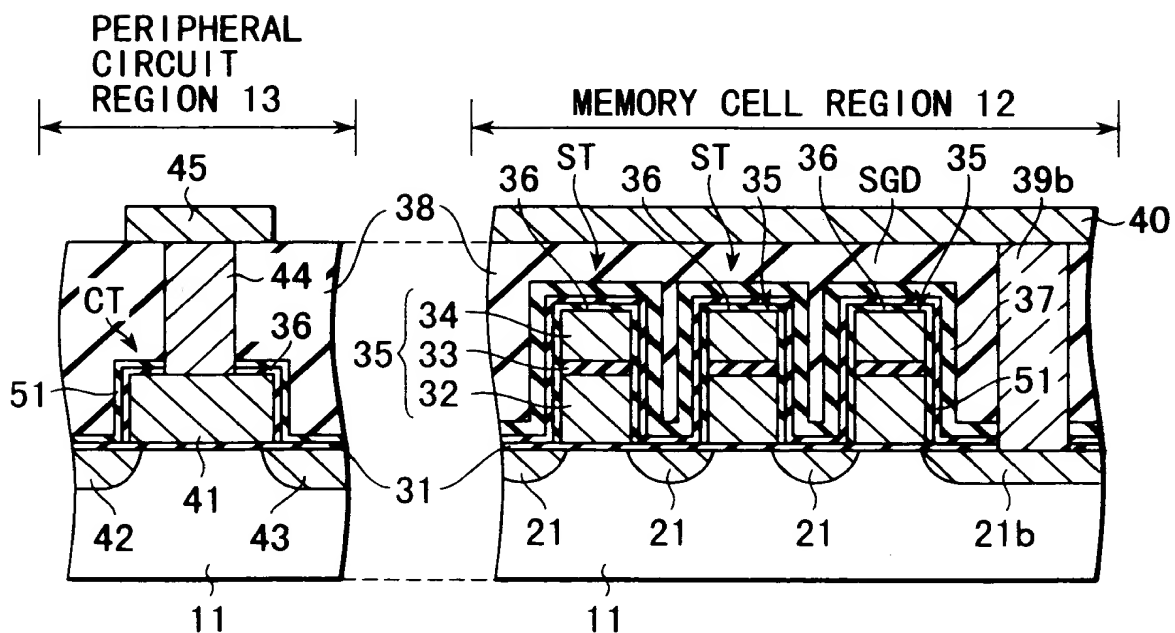


FIG. 12

005240" 2295560

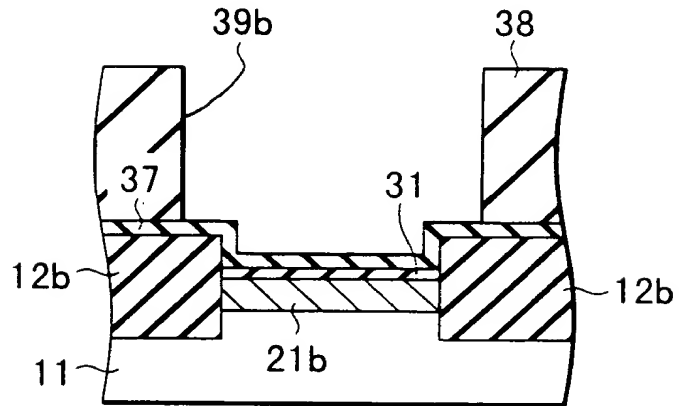


FIG. 10A

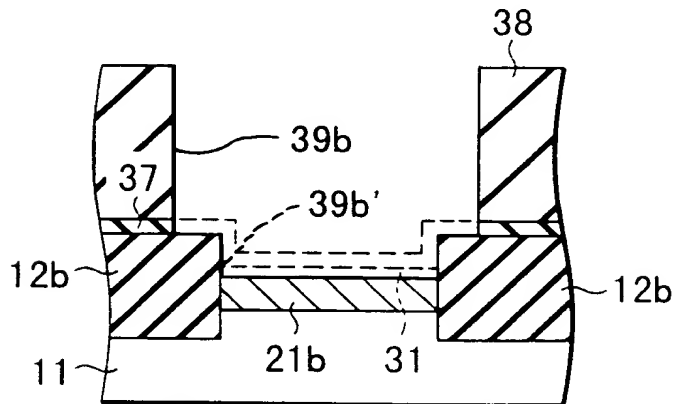


FIG. 10B

005240" 2/29/95

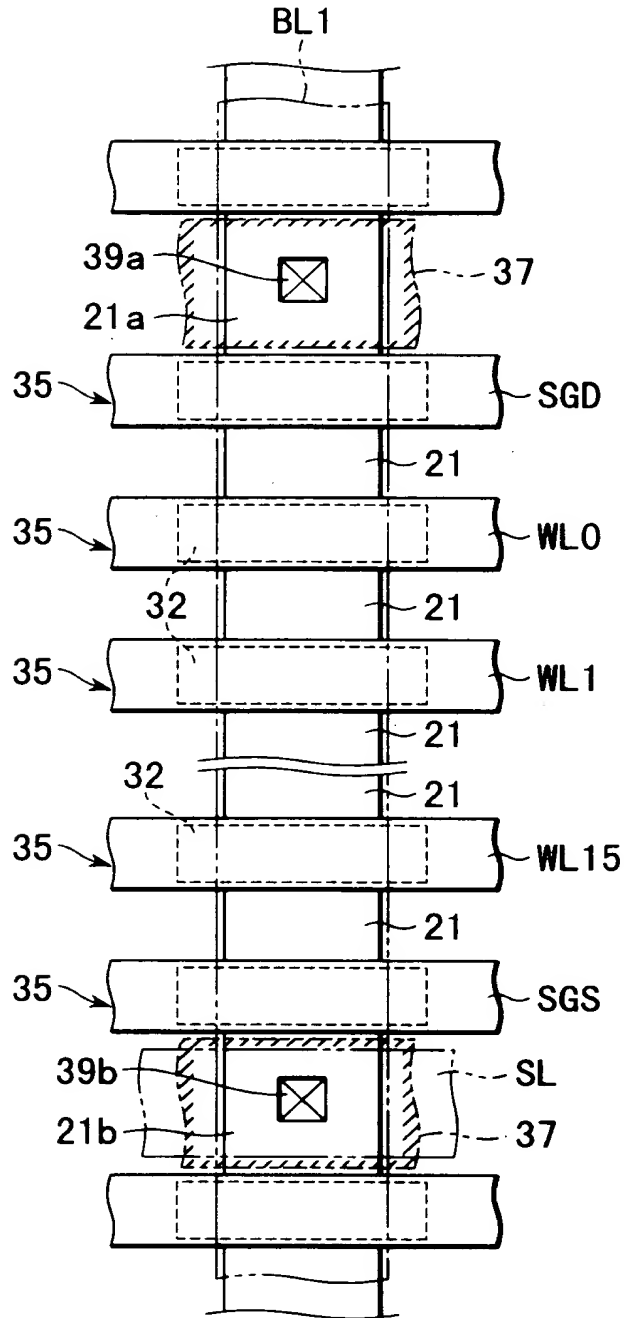


FIG. 11

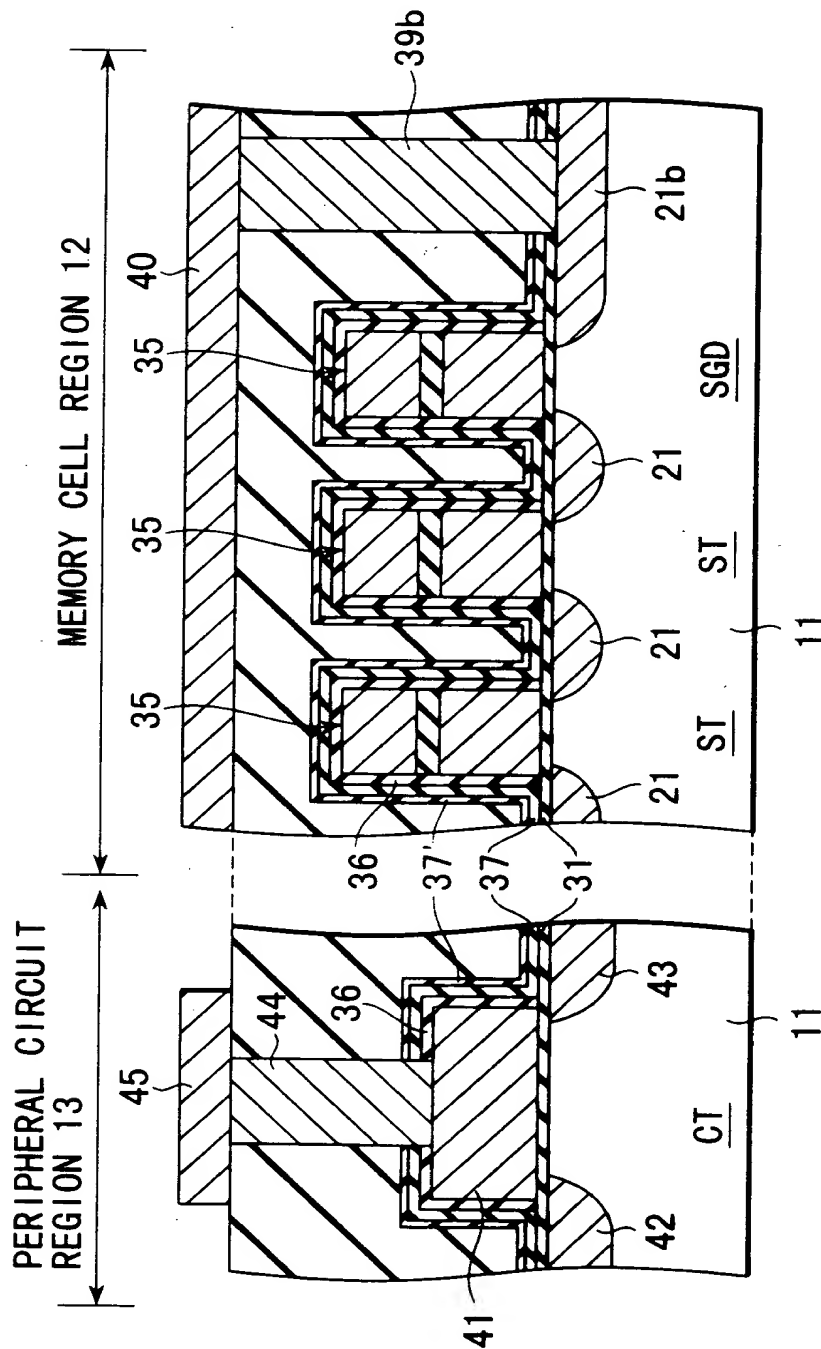
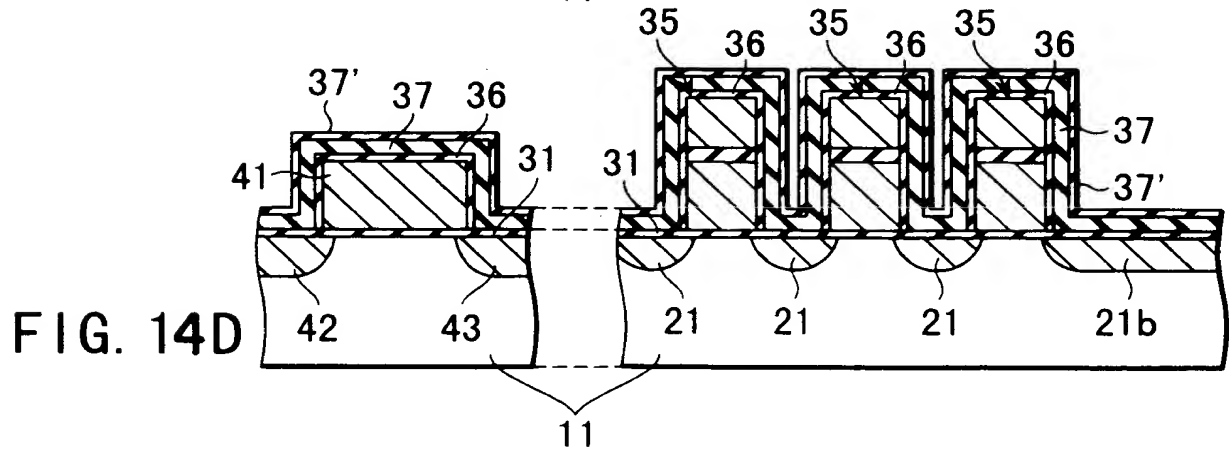
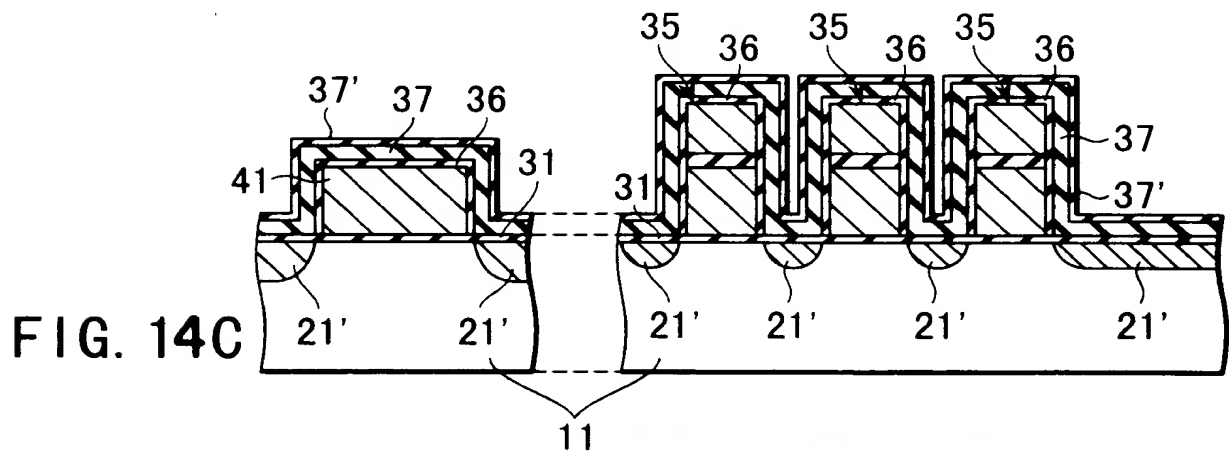
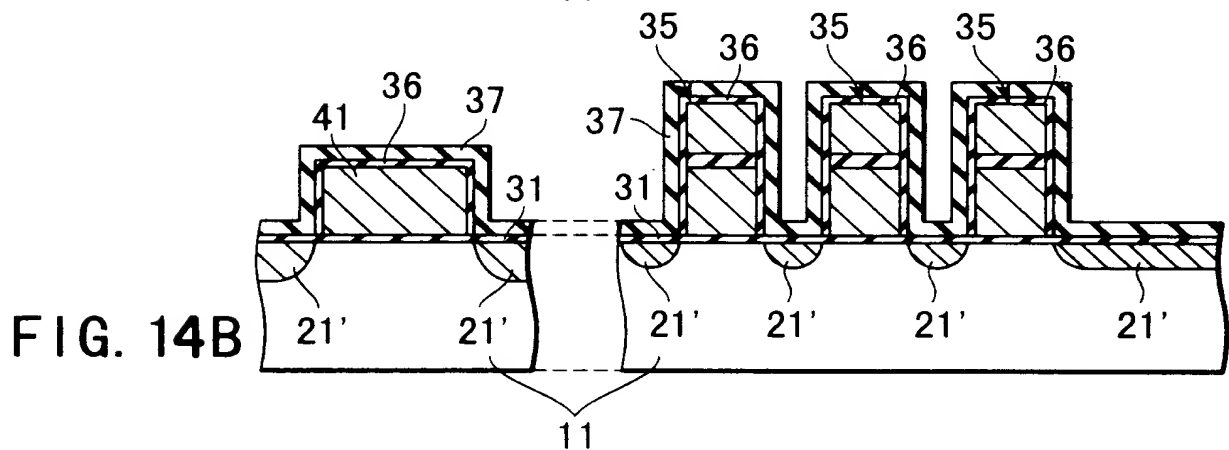
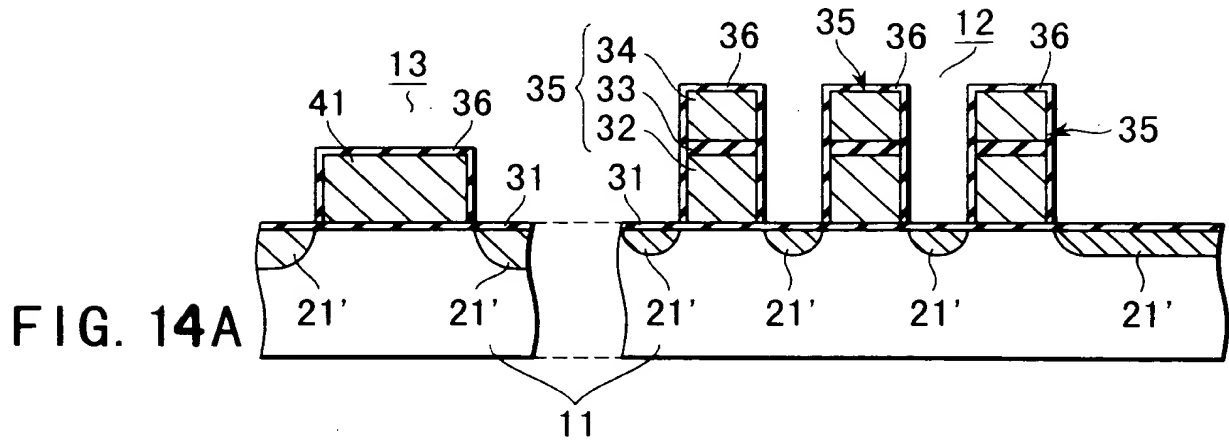


FIG. 13



005240 2295560

	CONCENTRATION OF HYDROGEN IN SiN FILM	CONCENTRATION OF HYDROGEN IN TUNNEL OXIDE FILM	dVg (ELECTRON AMOUNT TRAP)
NO SURFACE OXIDE FILM	4.0×10^{21} atom/cm ³	1	512mV
SURFACE OXIDE FILM FORMED	1.6×10^{21} atom/cm ³	0.2	398mV

FIG. 15

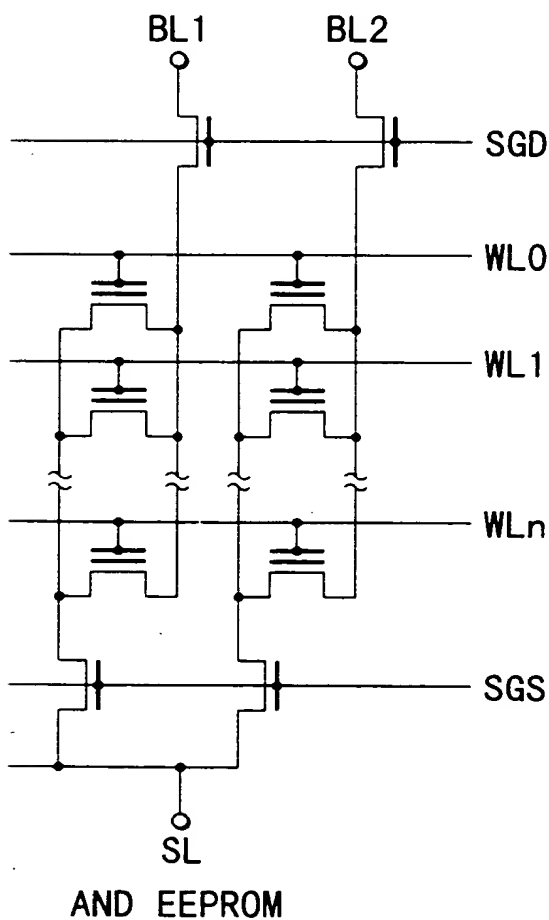


FIG. 16A

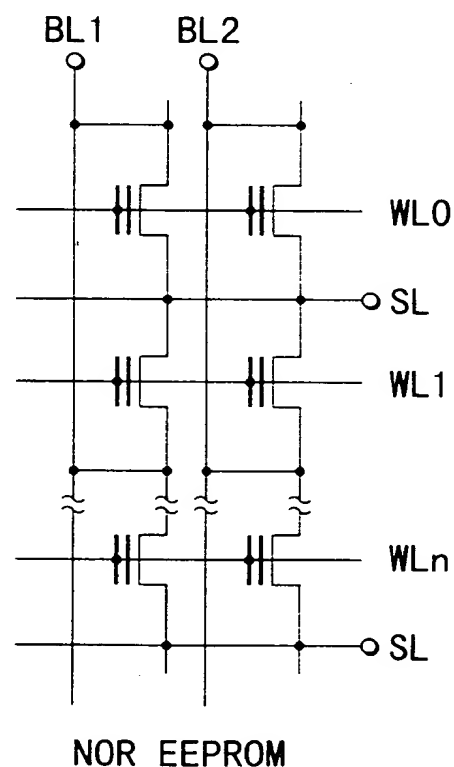


FIG. 16B

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